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5780 Mollie

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Gormley et al.

GROUP: 2811

SERIAL NO: 09/661,766

EXAMINER: Hung K. Vu

FILED: September 14, 2000

FOR: A METHOD FOR FORMING A SEMICONDUCTOR DEVICE AND A SEMICONDUCTOR DEVICE FORMED BY THE METHOD

Assistant Commissioner of Patents
Washington, D.C. 20231
Box Non-Fee Amendment

Sir:

AMENDMENT

In response to the Office Action mailed November 11, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

- B1
- 1 1. (Amended) A method for forming a semiconductor device comprising first, second
 - 2 and third layers, with a component being formed in the second layer, and first and second
 - 3 etch stop layers being located between the first and second layers, and the second and
 - 4 third layers, respectively, and at least the second etch stop layer being bonded to one of
 - 5 the second and third layers, the method comprising the steps of:
 - 6 prior to bonding the second etch stop layer to the one of the second and third
 - 7 layers, patterning the second etch stop layer to define the component in the second layer
 - 8 for facilitating etching of the second layer through the third layer,
 - 9 bonding the second etch stop layer to the one of the second and third layers, and